## Emerging thin film photovoltaic inorganic materials: kesterite and beyond

S. Giraldo<sup>1</sup>, Y. Sánchez<sup>1</sup>, M. Placidi<sup>1</sup>, Z. Jehl<sup>1</sup>, V. Izquierdo-Roca<sup>1</sup>,

A. Pérez-Rodríguez<sup>1,2</sup>, and **E. Saucedo<sup>1,3,\*</sup>** 

<sup>1</sup>Catalonia Institute for Energy Research (IREC), Sant Adrià del Besòs-Barcelona, Spain

<sup>2</sup>IN2UB, Departament d'Electrònica, Universitat de Barcelona, Barcelona, Spain

<sup>3</sup>Electronic Engineering Department, Polytechnic University of Catalonia (UPC), Barcelona, Spain

\*e-mail: esaucedo@irec.cat







## **Presentation of CUSTOM-ART project**

- 1. Introduction
- 2. Characteristics and challenges of kesterite
- 3. Doping and alloying strategies
- 4. Beyond kesterites
- 5. Conclusions and perspectives

#### **CUSTOM-ART – H2020-LC-SC3-2020-RES-IA-CSA-952982**

# Disruptive kesterite-based thin film technologies customized for challenging architectural and active urban furniture applications

**Main Objective:** CUSTOM-ART will demonstrate that the new generation of CZTS -based solutions developed and tested during the project, will become the most robust and cost-effective thin-film technology in the EU for challenging and demanding architectural and urban furniture applications.

#### Partners:



## Main characteristics:

- ✓ Demonstration at solar cell level of a performance  $\eta$ ≥20% and at module level of a  $\eta$ ≥16%.
- ✓ Fabrication of large size module prototypes: 1) Monograin module (20x20 cm<sup>2</sup>; 6.4Wp)) and 2) Micro-crystalline module onto steel (5x10 cm<sup>2</sup>; 0.8Wp).
- ✓ Demonstration in 4 DEMO-Sites (curved façades, curved tiles, bus canopy and urban furniture)



Seville Spain



Coordinator: Prof. Dr. Edgardo Saucedo (UPC and IREC) Duration: 09/2020 – 02/2024 Total budget: 6.999.745,25 € <u>www.custom-art-h2020.eu</u>





Presentation of CUSTOM-ART project

- 1. Introduction
- 2. Characteristics and challenges of kesterite
- 3. Doping and alloying strategies
- 4. Beyond kesterites
- 5. Conclusions and perspectives



- Main commercially available thin film PV technologies: CdTe and CIGSe
- In, Ga and Te identified by the European Commission as critical raw materials

#### 1. INTRODUCTION

#### JPhys Energy

#### TOPICAL REVIEW · OPEN ACCESS

#### Emerging inorganic solar cell efficiency tables (Version 1)

Lydia H Wong<sup>1</sup>, Andriy Zakutayev<sup>2</sup>, Jonathan D Major<sup>3</sup>, Xiaojing Hao<sup>4</sup>, Aron Walsh<sup>5,6</sup>, Teodor K Todorov<sup>7</sup> and Edgardo Saucedo<sup>8,9</sup>

Journal of Physics: Energy, Volume 1, Number 3

#### 4961 Total downloads



Turn on MathJax

Share this article

Material	Eff. (%)	V <sub>oc</sub> (V)	J <sub>sc</sub> (mA/cm²)	F.F. (%)	Area (cm <sup>2</sup> )	E <sub>g</sub> (eV)	Institutions
Cu <sub>2</sub> ZnSnS <sub>4</sub> (CZTS)	11.0±0.2	0.731	21.74	69.3	0.2339	1.5	UNSW. <sup>[3]</sup>
Cu <sub>2</sub> BaSnS <sub>4</sub> (substrate)	1.7	0.698	5.3	46.9	0.2	2.01	Central South University, UNSW, Shen Zhen University, Xiamen University. <sup>[19]</sup>
Cu <sub>2</sub> BaSnS <sub>4</sub> (superstrate)	2.0	0.933	5.1	42.9	0.2	2.04	The University of Toledo. <sup>[20]</sup>
Cu <sub>2</sub> FeSnS <sub>4</sub>	3.0	0.610	9.3	52.0	0.1	1.5	Indian Association for the Cultivation of Science. <sup>[21]</sup>
Cu <sub>2</sub> CdSn(S <sub>0.xx</sub> Se <sub>0.yy</sub> ) <sub>4</sub>	2.8	0.356	18.8	41.6	0.405	1.55	Changchun Institute of Applied Chemistry, Chinese Academy of Sciences. <sup>[22]</sup>
Cu <sub>2</sub> BaSn(S <sub>0.xx</sub> Se <sub>0.yy</sub> ) <sub>4</sub>	5.2	0.611	17.4	48.9	0.425	1.55	Duke University, IBM. <sup>[23]</sup>
Cu <sub>2</sub> ZnGe(S <sub>0.xx</sub> Se <sub>0.yy</sub> ) <sub>4</sub>	6.0	0.617	NA	NA	0.25	1.47	ZSW, CNRS. <sup>[24]</sup>
Cu <sub>2</sub> ZnGeSe <sub>4</sub>	7.6	0.558	22.8	59.0	0.5	1.36	CNRS, IMEC. <sup>[25]</sup>
Ag <sub>2</sub> ZnSnSe <sub>4</sub>	5.18	0.504	21.0	48.7	0.45	1.35	IBM, UCSD. <sup>[26]</sup>
Cu <sub>2</sub> (Zn <sub>0.6</sub> Cd <sub>0.4</sub> )SnS <sub>4</sub>	11.0	0.650	25.5	66.1	0.22	1.38	University of New South Wales, Australia; National Renewable Energy Laboratory, United States; Central South University, China. <sup>[27]</sup>
(Ag <sub>0.05</sub> Cu <sub>0.95</sub> ) <sub>2</sub> (Zn <sub>0.75</sub> Cd <sub>0.25</sub> )Sn <sub>4</sub>	10.1	0.650	23.4	66.2	0.16	1.4	NTU, Singapore; HZB, Germany. <sup>[29]</sup>

#### Several kesterite type materials at the forefront of the emerging thin film photovoltaic materials



Presentation of CUSTOM-ART project

- 1. Introduction
- 2. Characteristics and challenges of kesterite
- 3. Doping and alloying strategies
- 4. Beyond kesterites
- 5. Conclusions and perspectives

#### **Kesterite: emerging thin film PV materials**



#### **Tetragonal structure (I4 space group)**

#### Advantages of kesterites:

- Exclusively formed by **low-toxicity** and earth **abundant elements**.
- **P-type conductivity** naturally due to intrinsic point defects.
- Direct band-gap semiconductor with a high absorption coefficient (~10<sup>4</sup> cm<sup>-1</sup>).
- Easily **tunable band-gap**, either controlling the S/Se ratio or with cation substitution.
- Highly **compatible** with **CIGS** technology.

#### **Kesterite: emerging thin film PV materials**



## **Tetragonal structure (I4 space group)**

#### **Challenges of kesterites:**

- Cu and Zn are iso-electronic elements: easy exchange in the lattice (anti-sites defects formation: Cu<sub>Zn</sub>, Zn<sub>Cu</sub>).
- Sn forms volatile species with Se and
   Sn exchange with the annealing atmosphere, Sn loss.
- Sn is a multi-valent element (Sn<sup>+2</sup> and Sn<sup>+4</sup>): formation of defects related to Sn valence.
- **Sn** strongly **interacts** with **alkaline** elements.
- **Zn** is a relatively **volatile** element.





Sn<sub>Zn</sub> related anti-sites introduces deep defects
 All of them are giant recombination traps

Most plausible origin of the high non-radiative recombination and low carriers life-time

\*Results obtained by Prof. A. Walsh Group (ICL) in STARCELL, Unpublished.

## How can we solve this issue?

How to avoid Sn related anti-sites?\*

 $\circ$  Zn-rich Additional Zn forms ZnS/ZnSe.

 $\odot$  Sn-poor The Cu-rich secondary phases are conductive.

 $\odot$  hole poor (n-type) The acceptor (Cu\_{Zn}) are too many.

#### Partial substitution by Ge:

- Ge related defects are less detrimental
- Higher efficiencies theoretically predicted



- Removes free e-
- Reduce recombination



\*Results obtained by Prof. A. Walsh Group (ICL) in STARCELL, Unpublished.

#### We can learn several things from CIGS...



"Progress and Perspectives of Thin Film Kesterite Photovoltaic Technology: A Critical Review", Sergio Giraldo, Zacharie Jehl, Marcel Placidi, Victor Izquierdo-Roca, Alejandro Pérez-Rodríguez, Edgardo Saucedo, Advanced Materials, Volume 31, Issue 16, 201806692, 2019.

- CuInSe<sub>2</sub> and Cu<sub>2</sub>ZnSnSe<sub>4</sub> About 2% efficiency difference
- CuInS<sub>2</sub> and Cu<sub>2</sub>ZnSnS<sub>4</sub>(Cd) About 1% efficiency difference
- Cu(In,Ga)Se<sub>2</sub> and Cu<sub>2</sub>ZnSn(S,Se)<sub>4</sub> About 10% efficiency difference



Presentation of CUSTOM-ART project

- 1. Introduction
- 2. Characteristics and challenges of kesterite
- 3. Doping and alloying strategies
- 4. Beyond kesterites
- 5. Conclusions and perspectives

## Extrinsic Doping



"Doping and alloying of kesterites", Yaroslav Romanyuk, Stefan Haass, Sergio Giraldo, Marcel Placidi, Devendra Tiwari, David Fermin, Xiaojing Hao, Hao Xin, Thomas Schnabel, Marit Kauk-Kuusik, Paul Pistor, Stener Lie and Lydia Helena Wong, J. Physics Energy 2019 (DOI: 10.1088/2515-7655)

#### Most relevant

Doping: alkali elements and Ge

57	58	59	60	61	62	63	64	65	66	67	68	69	70	71
La	Ce	Pr	Nd	Pm	Sm	Eu	Gd	Tb	Dy	Ho	Er	Tm	Yb	Lu
Lanthanum	Cerium	Praseodymium	Neodymium	Promethium	Samarium	Europium	Gadolinium	Terbium	Dysprosium	Holmium	Erbium	Thulium	Ytterbium	Lutetium
89	90	91	92	93	94	95	96	97	98	99	100	101	102	103
Ac	Th	Pa	U	Np	Pu	Am	Cm	Bk	Cf	Es	Fm	Md	No	Lr
Actinium	Thorium	Protactinium	Uranium	Neptunium	Plutonium	Americum	Curium	Berkelium	Californium	Einsteinium	Fermium	Mendelevium	Nobelium	Lawrencium

#### What is the best alkaline dopant?

Author	Order of performance improvement
Mule et al. Thin Solid Films 2016	Na > Cs > K > Rb > Li
Hsieh et al. Adv. Energy Mater. 2016	K > Rb > Na > Li > Cs
Altamura et al. Scientific Reports 2016	Li > Na > Rb
López-Marino et al. J. Mater. Chem. A 2016	K > Na
S. Haass et al. Adv. Energy Mater. 2017	Li > Na > K > Rb > Cs

- ✓ Some discrepancy in the literature about the most efficient alkaline
- ✓ Effect on morphology quite well documented
- ✓ Role of each of them is still matter of intensive research
- ✓ PAT (or doping before/during the annealing) more effective than PDT for the moment
- Lighter elements more effective than heavier elements for the moment

#### Brief review on alkaline doping...



- ✓ For each alkali metal adjustment of Sn content and alkali concentration is mandatory!\*
- ✓ Strong interaction with Sn
- $\checkmark$  This is something very particular of kesterites, and no yet understood
- ✓ Li > Na > K > Rb > Cs

\*Stefan G. Haass et al., Adv. Energy Mater. 2018, 8, 1701760.



✓ Li has been demonstrated as a relevant doping and alloying element to improve kesterite efficiency
 ✓ Li<sup>+</sup> is the most similar cation to H<sup>+</sup>



## Is this related to the technological solution proposed by ICL in STARCELL????

I have no idea!!!! But at least is very promising!!!

#### **1. INTRODUCTION**

#### 2. CHALLENGES

#### **3. DOPING-ALLOYING**





✓ Ge has been demonstrated as a relevant doping and alloying element to improve kesterite efficiency

 $\checkmark$  Ge<sup>+4</sup> substitutes Sn<sup>+4</sup> in the kesterite structure

## **Extrinsic Doping**

1 IA					Kest Desr	erite ibed	elen in th	nents lis re	s view	:							18 VIIIA
1			Dopants														
Hydrogen	2 IIA					ΔIIc	wing	(> 1)	at%)			13 IIIA	14 IVA	15 VA	16 VIA	17 VIIA	Helium
3	4					7 110	פיייע <i>י</i>	. (~ ±	ut/0j			5	6	7	8	9	10
Li	Be				Othe	er rep	orte	d				B	С	Ν	0	F	Ne
Lithium 11	12											13	Carbon 14	Nitrogen 15	16	Florine 17	18
Na	Mg							VIIIB -				AI	Ci	P	S	CI	Ar
Sodium	Magnesium	3 IIIB	4 IVB	5 VB	6 VIB	7 VIIB	8 '	9	10 '	11 IB	12 IIB	Aluminiy	Silicon	Phosphorus	Sulfur	Chlorine	Argon
19	20	21	22	23	24	25	26	27	28	29	30	31	32	33	34	35	36
K		Scandium	Ti Titanium	Vanadium	Cr	Manganese	Fe	Cobalt		Cu	Zn	Gallit	Germanium	AS	Selenium	Br	Krypton
37	38	39	40	41	42	43	44	45	46	47	48	49	50	51	52	53	54
Rb	Sr	Y	Zr	Nb	Mo	Тс	Ru	Rh	Pd	Ag	Cd	In	Sn	Sb	Те	I	Xe
Rubidium	Strontium	Yttrium	Zirconium	Niobium	Molybdenum	Technetium	Ruthenium	Rhodium	Palladium	Silver	Cadmium	Indium	Tin	Antimony	Tellurium	lodine OE	Xenon
55	56	57-71	12	-73 -		75 D-	<b>^</b>		<sup>78</sup>	19	80	81	82	83	84 D	60 A 1	00 Dua
Caesium	Barium		HT	la Tantalum	Tungsten	Rhenium	Osmium		Platinum	Gold	Hg	Thallium	PD	Bismuth	Polonium	AL	Radon
87	88		104	105	106	107	108	109	110	111	112	113	114	115	116	117	118
Fr	Ra	89-103	Rf	Dubnuir	Seaborgium	Bh	Hassium	Mt	Ds	Rg	Copernicium	Nh	Flerovium	Mc	Lv	Ts	Oganesson
. ranoiali									1								

57	58	59	60	61	62	63	64	65	66	67	68	69	70	71
La	Ce	Pr	Nd	Pm	Sm	Eu	Gd	Tb	Dy	Ho	Er	Tm	Yb	Lu
Lanthanum	Cerium	Praseodymium	Neodymium	Promethium	Samarium	Europium	Gadolinium	Terbium	Dysprosium	Holmium	Erbium	Thulium	Ytterbium	Lutetium
89	90	91	92	93	94	95	96	97	98	99	100	101	102	103
Ac	Th	Pa	U	Np	Pu	Am	Cm	Bk	Cf	Es	Fm	Md	No	Lr
Actinium	Thorium	Protactinium	Uranium	Neptunium	Plutonium	Americum	Curium	Berkelium	Californium	Einsteinium	Fermium	Mendelevium	Nobelium	Lawrencium

- ✓ Ge and Li are the only elements proved as efficient doping/alloying solutions
- ✓ Both of them demonstrates a strong interaction with Sn

 ✓ Something wrong happens with Sn.
 ✓ To understand and solve it can be one of the breakthrough for increasing the conversion efficiency

## Alloying



58 59 60 61 62 63 64 65 66 67 68 69 70 71 57 Ce Pr Nd Pm Sm Eu Gd Tb Dy Ho Er Tm Yb Lu La Erbium Thulium Terbium Ytterbium Lutetium 100 101 102 89 90 91 92 93 95 96 97 98 99 103 94 Ра Pu Am Cm Bk Cf Fm Md No Ac Th U Np Es Lr "Doping and alloying of kesterites", Yaroslav Romanyuk, Stefan Haass, Sergio Giraldo, Marcel Placidi, Devendra Tiwari, David Fermin, Xiaojing Hao, Hao Xin, Thomas Schnabel, Marit Kauk-Kuusik, Paul Pistor, Stener Lie and Lydia Helena Wong, J. Physics Energy 2019 (DOI: 10.1088/2515-7655)

#### Most relevant

Alloying: Li, Mn, Ag, Cd and Ge

Cu<sub>2</sub>ZnSn(S,Se)<sub>4</sub> Mn,Cd Ge Li,Ag

## Lithium\*: substitutes Cu



- ✤ Up to 12% Li alloying
- Large efficiency improvement with 3-7% Li (mainly Voc and FF improved)
- \* Increase in the apparent carrier concentration with Li
- Increase of the quantum yield
- No improvement in the minority carrier life-time
- Efficiency up to 12.2% is obtained

\*Cabas-Vidani A, Haass S G, Andres C, Caballero R, Figi R, Schreiner C, Márquez J A, Hages C, Unold T, Bleiner D, Tiwari A N and Romanyuk Y E 2018 High-Efficiency  $(\text{Li}_x\text{Cu}_{1-x})_2\text{ZnSn}(S,\text{Se})_4$  Kesterite Solar Cells with Lithium Alloying *Adv. Energy Mater.* **8** 1801191

Silver\*: substitutes Cu



- Decent efficiencies have been reported using Ag in substitution of Cu<sup>[1]</sup>
- Band-gap suitable for graded E<sub>q</sub> concepts
- Has shown to probably solve one of the main issues of kesterites: Cu-Zn disorder, most probably related to a change of the structure from kesterite to stannite
- Problems:
- o change of conductivity for high Ag concentrations
- Ag is expensive

#### Silver\*: substitutes Cu





- Possibility to tune the band-gap has been demonstrated\*
- ✤ Ag seems to help to improve the efficiency of the devices
- Nevertheless, possibility of band-gap grading is not demonstrated
- The feasibility is in doubt, cause the high mobility of Cu ions, and the large quantity of Cu vacancies in kesterite

## Manganese\*: substitutes Zn



- Substitution of Zn with Mn in CZTSSe thin films is shown to induce structural transformation at x = 0.2 which is largely attributed to the difference in the atomic radius
- The variation of the Mn content is also found to change the charge density, mobility and carrier lifetime in CMZTSSe
- Improvement in the conversion efficiency of solar cell devices is observed for low Mn contents
- The improved open circuit voltage (Voc) and fill factor (FF) are attributed to the improved shunt resistance and carrier transport due to lower defect density especially at the CdS/CMZTSSe interface
- If Mn content is more than 5% (x > 0.05), the efficiency was reduced due to the significant increase of carrier density

\*Lie S, Rui Tan J M, Li W, Leow S W, Tay Y F, Bishop D M, Gunawan O and Wong L H, "Reducing the interfacial defect density of CZTSSe solar cells by Mn substitution", J. Mater. Chem. A 6 1540–50, 2018.

#### Cadmium\*: substitutes Zn



Figure 5. (a) J-V curves and (b) EQE curves of CZTS and champion CZCTS devices.

#### Table 2. Device Characteristics of the CZTS and CZCTS Solar Cells

absorber	$V_{\alpha c}$ (mV)	$J_{sc}$ (mA/cm <sup>2</sup> )	FF (%)	Eff (%)	$E_g/q_V V_{oc}$ (mV)	$R_{\rm S,L}$ ( $\Omega$ cm <sup>2</sup> )	$G_{4,L}$ (mS cm <sup>-2</sup> )	A	$J_0$ (A/cm <sup>2</sup> )
CZTS	683	20.7	62.5	8.8	847	0.96	0.67	3.3	$8.1 \times 10^{-6}$
CZCTS	650	26.7	66.1	11.5	730	0.45	1.0	2.5	$1.2 \times 10^{-6}$



- Suitable for the S or S/Se compound
- Cd alloying into CZTS can improve the microstructure by facilitating the growth of larger grains and change the nature of the secondary phases of the absorber
- Alloying of Cd in CZTS can reduce the Voc deficit and recombination by reducing the band tailing problem
- Alloying of Cd can increase minority carrier lifetime and lowers the doping density (free carrier)
- Cd incorporation elevates the VBM position of CZTS rather than lower the CBM position of CZTS, suggesting an undesirable cliff-like heterojunction interface
- Efficiencies over 11% are achieved

#### Cadmium\*: substitutes Zn



- Recent reported 10% certified efficiency solar cell in large area (>1cm<sup>2</sup>) (11% in standard size)
- Inter-diffusion of CZTS/CdS (selective surface alloying/doping)
- Elemental inter-diffusion: Zn into CdS and Cd into CZTS
- Na accumulation and local Cu depletion at the heterojunction
- ✤ New phases formation: Cu<sub>2</sub>Cd<sub>x</sub>Zn<sub>1-x</sub>SnS<sub>4</sub>, Zn<sub>x</sub>Cd<sub>1-x</sub>S, and Cu<sub>2-x</sub>Na<sub>x</sub>ZnSnS<sub>4</sub>.
- More favorable band-alignment is demonstrated and recombination at the hetero-junction is reduced

\*Yan, Chang; Huang, Jialiang: Sun, Kaiwen; Johnston, Steve; Zhang, Yuanfang; Sun, Heng; Pu, Aobo; He, Mingrui; Liu, Fangyang; Eder, Katja; Yang, Limei; Cairney, Julie M.; Ekins-Daukes, N. J.; Hameiri, Ziv; Stride, John A.; Chen, Shiyou; Green, Martin A.; Hao, Xiaojing, "Cu2ZnSnS4 solar cells with over 10% power conversion efficiency enabled by heterojunction heat treatment", Nature Energy 3 (9) 764-772, 2018.

#### Germanium: substitutes Sn



First group reporting Ge alloyed CZTSe with Eff > 10%: [1]

- Improved morphological properties: flat surfaces, dense morphologies, and large grains.
- Highest efficiency of 10.03%, with an open-circuit voltage (V<sub>oc</sub>) of 0.54 V, as well as an improved V<sub>oc</sub> deficit of 0.647 V



Study of CZTGeSSe devices as function of Ge/(Ge+Sn) rel. content using spray coated absorbers with molecular inks: <sup>[3]</sup>

Highest efficiency: 11.0% with 25%Ge relative content (band gap of about 1.2 eV) with reduction of V<sub>oc</sub> deficit

[1] S. Kim et al, Sol. Energy Mater. Sol. Cells. 2016, 144, 488-492 [2] S. Kim et al. Appl. Phys. Express 2016, 9, 102301



Best efficiency reported for Ge alloyed CZTSe: [2]

- Conversion efficiency of 12.3%
- Improved V<sub>oc</sub> deficit of 0.583 V and FF of 72.7%
- Reduced band tailing and carrier recombination.



Nanocrystal-based CZTGeSSe absorbers with tunable band gap: [4]

- Maximum conversion efficiencies of up to 9.4% are achieved with a Ge content of 30 at.%
- Enhanced performance due to increased minority charge carrier lifetimes as well as reduced voltage-dependent charge carrier collection.

[3] A.D. Collord, H.W. Hillhouse. Chem. Mater. 2016, 7, 2067–2073
[4] C.J. Hages et al, Prog. Photovoltaics Res. Appl. 2015, 23, 376–384

## Bonus!: double cation substitution (Cd, Ag)



- Double cation substitution can be used to improve upon the device performance achievable via single cation substitution, if the two cations affect different limiting factors of CZTS.
- Cd alters the position of acceptor defects near the valence band, and the maximum device performance is obtained at the Cd content corresponding to the shallowest acceptor defects.
- Ag decreases the charge carrier density, improves the photoluminescence decay time and efficiency, as well as the open-circuit voltage, indicating a reduction of the nonradiative recombination via defects.
- Double cation substitution can be used as a tool to fine-tune the properties of the absorber material.
- Efficiencies over 10% are reported (5% Ag and 25% of Cd)

\*Shreyash H. Hadke, Sergiu Levcenko, Stener Lie, Charles J. Hages, José A. Márquez, Thomas Unold, and Lydia H. Wong, "Synergistic Effects of Double Cation Substitution in Solution-Processed CZTS Solar Cells with over 10% Efficiency", Adv. Energy Mater. 2018, 8, 1802540.

**3. DOPING-ALLOYING** 

### Summary\*

Material	Doping element	Eg (eV)	Voc (mV)	Eff (%, total area)	Ref
CZTSSe	nominally undoped*	1.13	513	12.6	[3]
CZTSSe	Li	1.04	449	11.5	[26]
CZTSe	Na*	1.0	423	11.6	[39]
CZTSe	К	1.02	432	9.7	[45]
CZTSSe	Rb	0.96	419	8.8	[26]
CZTSSe	Cs	0.97	439	9.1	[26]
CZTSe	In	1.02	423	7.8	[82]
CZTSe	Ge	1.04	463	11.8	[106]

Material	Alloying element	Eg (eV)	V <sub>oc</sub> (mV)	Eff. (%, total area)	Ref.
ACZTSSe	Ag/(Ag+Cu)=3%	1.07	448	10.4	[57]
CMZTSSe	Mg/(Mg+Zn)=4%	1.01	419	7.2	[72]
CZCTS	Cd/(Cd+Zn)=40%	1.38	650	11.5	[75]
CZTGSe	Ge/(Ge+Sn)=22%	1.11	527	12.3	[113]
CMZTS	Mn/(Mn+Zn)=5%	1.055	418	8.9	[142]
ACZCTSSe	Ag: 5%, Cd:25%	1.4	650	11.1	

✤ Most promising doping elements: Li, Na and Ge

Most promising alloying elements: Cd and Ge, maybe double cation substitution?

\*"Doping and alloying of kesterites", Yaroslav Romanyuk, Stefan Haass, Sergio Giraldo, Marcel Placidi, Devendra Tiwari, David Fermin, Xiaojing Hao, Hao Xin, Thomas Schnabel, Marit Kauk-Kuusik, Paul Pistor, Stener Lie and Lydia Helena Wong, J. Physics Energy 2019 (DOI: 10.1088/2515-7655)



Presentation of CUSTOM-ART project

- 1. Introduction
- 2. Characteristics and challenges of kesterite
- 3. Doping and alloying strategies
- 4. Beyond kesterites
- 5. Conclusions and perspectives

#### You are very lucky!!!..

IOP Publishing J. Phys.: Energy 1 (2019) 032001

https://doi.org/10.1088/2515-7655/ab2338

#### JPhys Energy

CroseMark	TOPICAL REVIEW									
CIOSSMAIK	Emerging inorganic solar cell efficiency tables (Version 1)									
OPEN ACCESS										
RECEIVED	Lydia H Wong <sup>1</sup> <sup>®</sup> , Andriy Zakutayev <sup>2</sup> <sup>®</sup> , Jonathan D Major <sup>3</sup> <sup>®</sup> , Xiaojing Hao <sup>4</sup> <sup>®</sup> , Aron Walsh <sup>5,6</sup> <sup>®</sup> , Teodor K Todorov <sup>7</sup> and Edgardo Saucedo <sup>8,9</sup> <sup>®</sup>									
29 March 2019	Todor K Todorov and Edgardo Sadecdo									
REVISED 17 May 2019	<ul> <li>Nanyang Technological University, 637553 Singapore, Singapore</li> <li>National Renewable Energy Laboratory, Golden, Colorado 80401, United States of America</li> </ul>									
ACCEPTED FOR PUBLICATION 21 May 2019	<ul> <li><sup>3</sup> University of Liverpool, Liverpool, L697ZF, United Kingdom</li> <li><sup>4</sup> University of New South Wales, Sydney, NSW 2052, Australia</li> </ul>									
PUBLISHED	<ul> <li><sup>5</sup> Imperial College London, London SW7 2AZ, United Kingdom</li> <li><sup>6</sup> Yonsei University, Seoul 03722, Republic of Korea</li> </ul>									
	<ul> <li><sup>7</sup> IBM Thomas J. Watson Research Center, New York 10598, United States of America</li> <li><sup>8</sup> Catalonia Institute for Energy Research (IREC), E-08930 Sant Adrià del Besòs- Barcelona, Spain</li> </ul>									
Original content from this work may be used under	<sup>9</sup> Author to whom any correspondence should be addressed.									
the terms of the Creative Commons Attribution 3.0	E-mail: lydiawong@ntu.edu.sg, andriy.zakutayev@nrel.gov, jon.major@liverpool.ac.uk, xj.hao@unsw.edu.au, a.walsh@imperial.ac.uk, tktodoro@us.ibm.com and esaucedo@irec.cat									
Any further distribution of this work must maintain attribution to the	Keywords: thin film inorganic photovoltaics, emerging photovoltaic technologies, solar energy, photovoltaic conversion efficiency tables									

• Since last year a group of international scientists we are compiling the Efficiency Tables of Emerging PV Inorganic Materials in collaboration with Institute of Physics of UK (IOP)

#### What options do we have?



Example: selection through the structure



J. Phys.: Energy 1 (2019) 032001 https://doi.org/10.1088/2515-7655/ab23 OXIDES JPhys Energy • Cu2O Bi2FeCrO6 **TOPICAL REVIEW** Emerging inorganic solar cell efficiency tables (Version 1) **PNICTIDES** Lydia H Wong<sup>1</sup><sup>(i)</sup>, Andriy Zakutayev<sup>2</sup><sup>(i)</sup>, Jonathan D Major<sup>3</sup><sup>(i)</sup>, Xiaojing Hao<sup>4</sup><sup>(i)</sup>, Aron Walsh<sup>5,6</sup><sup>(i)</sup>, Teodor K Todorov<sup>7</sup> and Edgardo Saucedo<sup>8,9</sup> (b) • InP • (In,Ga)N CHALCOGENIDES • (Zn,Sn)N2 • Se Cu2FeSnS4 • GeSe HALIDES Cu2ZnGeSe4 • PbS Ag2ZnSnSe4 Sb2Se3 • Bil3 • (Li,Cu)2ZnSn(S,Se)4 • Sb2S3 CsPbBr3 • Cu2(Zn,Mn)Sn(S,Se)4 • Bi2S3 CsPbI3 Cu2BaSnSe4 • SnS CsSnBr3 Cu2BaSnS4 AgBiS2 CsSnI3 Cu2ZnSnSe4 Cu2SnS3 • Cs(Sn,Ge)I3 Cu2ZnSnS4 CuSbS2 Cu2CdSnS4 CuSbSe2

- Few oxides and pnictides
- Some halides but increasing interest
- Several chalcogenides, from simple to multinary compounds





## LOW DIMENSIONAL SEMICONDUCTORS FOR OPTICALLY TUNEABLE SOLAR HARVERSTERS

## H2020-ERC-CoG-2019-866018

Project Coordinator: Prof. Dr. Edgardo Saucedo (Polytechnic University of Catalonia)

Starting date: 1<sup>st</sup> June 2020 (5 years)

## THE SENSATE INNOVATIONS

## **Q-1D PV Absorbers**

*High throughput screening* of (Ge,Sn,Sb,Bi):

- Ghalcogenides
   Ghal
- Halides
- Mixed chalco-halides

Best suited anisotropic **Q-1D** materials with "A la carte" **tuneable optical/electrical** properties





## Selective contacts with dipoles

*Bi-layer* nano-scale asymmetric contact structure:

- p- and n-type transition metal oxides already developed at IREC
- Dipolar organic and inorganic molecules

Very efficient charges extraction creating highly asymmetric polarized interfaces



Presentation of CUSTOM-ART project

- 1. Introduction
- 2. Characteristics and challenges of kesterite
- 3. Doping and alloying strategies
- 4. Beyond kesterites
- 5. Conclusions and perspectives

#### CONCLUSIONS AND PERSPECTIVES

Something happens with Sn! Maybe there one of the solutions to increase the efficiency is waiting for us.

BEYOND KESTERITE

- Oxides, Pnictides, Chalcogenides, Halides...examples in the literature abound
- ERITE Among them, perovskite halides and anisotropic chalcogenides are at the forefront for the moment in terms of efficiency

\* We are facing the revolution of the non-cubic/non-tetragonal materials!!!???

#### ACKNOWLEDGMENTS











## H2020-ERC-CoG-2019-866018

To the organizing Committee: Alex Redinger, Amit Munshi, Jiro Nishinaga, Negar Naghavi, Romain Carron, Rutger Schlatmann, and Sophie Spangenberger



Virtual Chalcogenide PV Conference 2020.

# Thanks for your attention!